

PATENT ASSIGNMENT

Electronic Version v1.1
 Stylesheet Version v1.1

SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	Ownership Transfer
CONVEYING PARTY DATA	
Name	Execution Date
NXP B.V.	05/29/2009
RECEIVING PARTY DATA	
Name:	IPDIA
Street Address:	2 Rue de la Girafe
City:	Caen
State/Country:	FRANCE
Postal Code:	14000
PROPERTY NUMBERS Total: 6	
Property Type	Number
Application Number:	12299325
Application Number:	12092607
Application Number:	12301405
Application Number:	12442351
Application Number:	12092608
Patent Number:	7311242
CORRESPONDENCE DATA	
Fax Number:	(612)455-3801
<i>Correspondence will be sent via US Mail when the fax attempt is unsuccessful.</i>	
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Correspondent Name:	James A. Larson/LAH
Address Line 1:	Hamre, Schumann, Mueller & Larson
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Address Line 4:	Minneapolis, MINNESOTA 55402
ATTORNEY DOCKET NUMBER:	20281.0012USWO

CH \$240.00 12299325

501234509

PATENT
REEL: 024686 FRAME: 0839

NAME OF SUBMITTER:

James A. Larson

Total Attachments: 7

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**INTELLECTUAL PROPERTY TRANSFER AND
LICENSE AGREEMENT**

between

NXP B.V.

and

IPDIA

INTELLECTUAL PROPERTY TRANSFER AND LICENSE AGREEMENT

THIS AGREEMENT IS MADE ON MAY 29, 2009, (THE "EFFECTIVE DATE") BY AND BETWEEN:

- (1) NXP B.V., a limited liability company incorporated under the laws of the Netherlands, with corporate seat in Eindhoven, the Netherlands, and having its address at High Tech Campus 60, 5656 AG Eindhoven, the Netherlands, (the "Seller"), represented by Mr. Jean-Yves Muller, who represents and warrants that he is fully empowered for the purposes of this agreement;

and

- (2) IPDIA, a French *société anonyme à directoire et conseil de surveillance* with a share capital of EUR 51,050, having its registered office located 7, rue Alfred Kastler, Immeuble Emergence, 14000 Caen, France, registered with the Registry of Commerce and Companies under number 512 603 861 (the "Purchaser"), represented by Mr. Franck Murray, who represents and warrants that he is fully empowered for the purposes of this agreement,

WHEREAS:

(A)

- (B) By this Intellectual Property Transfer and License Agreement, the Parties wish to set out the terms and conditions applicable to the assignment, transfer and licensing of certain intellectual property (rights) to Purchaser in connection with the divestment, pursuant to and in accordance with the Asset Purchase Agreement (as defined hereinafter). The provisions of the Asset Purchase Agreement shall apply to the present Agreement unless otherwise specified.

IT IS AGREED AS FOLLOWS:

1 INTERPRETATION

1.1 Definitions

When used in this Agreement, the following capitalised terms shall have the meanings set forth below:

"A-Patents" means the Patent Assets listed in Annex A;

2 ASSIGNMENT AND LICENSE BACK OF A-PATENTS

2.1 Assignment and license back

2.1.1 Subject to the provisions of this Clause 2, Seller hereby assigns, transfers and conveys, and shall procure the assignment, transfer and conveyance by its respective Affiliates, to Purchaser all of Sellers entire right, title and interest in and to the A-Patents as per the Closing Date.

2.1.2

2.1.3

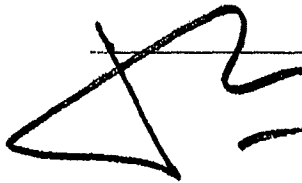
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2.3

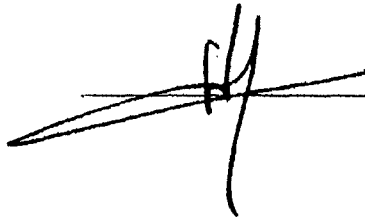
2.4

AGREED AND SIGNED ON MAY 29, 2009 BY:

Name: NXP B.V., as the Seller
By: Mr. Jean-Yves Muller

A handwritten signature in black ink, consisting of a large, stylized 'J' and 'M' with a horizontal line through the middle, positioned over a horizontal line.

Name: IPDIA, as the Purchaser
By: Mr. Franck Murray

A handwritten signature in black ink, consisting of a stylized 'F' and 'M' with a horizontal line through the middle, positioned over a horizontal line.

Annex A – Patents for transfer

Record ID	Patent Family	App Title	Country	Filed Date	App #	Grant Date	Patent #
81112643	FR020019WO	ISOLATED CAVITY CREATION	Patent				
			Cooperation	11 Mar 2003	IB2003/000938		
			Treaty				
			United States of America	11 Mar 2003	10/507332	25 Dec 2007	7311242
			Japan	11 Mar 2003	2003-577335		
81112642	FR020019FRN	ISOLATED CAVITY CREATION	France	19 Mar 2002	0203370		
81112641	FR020019EP	ISOLATED CAVITY CREATION	European Patent	11 Mar 2003	03744488.8		
81112640	FR020019CN	ISOLATED CAVITY CREATION	China	11 Mar 2003	03806026.4	24 Dec 2008	03806026.4
81138935	GB040246WO	INTEGRATED WAFER-LEVEL PACKAGING (IWLP)	Patent				
			Cooperation	08 Dec 2005	IB2005/054119		
			Treaty				
			United States of America	08 Dec 2005	11/721435		
			Taiwan	07 Dec 2005	094143257		
81114087	GB040246TW	INTEGRATED WAFER-LEVEL PACKAGING (IWLP)	Taiwan	07 Dec 2005	094143257		
81114086	GB040246EPP	INTEGRATED WAFER-LEVEL PACKAGING (IWLP)	European Patent	10 Dec 2004	04300878.8		
81381368	81047870WO02	Method to increase throughput of high AR holes or trenches	Patent				
			Cooperation	30 Dec 2008	IB2008/055579		
			Treaty				
81352587	81047870EP01	Method to increase throughput of high AR holes or trenches	European Patent	16 Jan 2008	08100543.1		
81363228	81058838EP01	Method for increasing throughput of high AR holes to meet emerging packaging requirements	European Patent	12 Aug 2008	08290769.2		
81381759	81057856EP01	Method to improve integrity of passivation layer	European Patent	17 Jun 2008	08290588.8		
81382880	006822US01	Network of vias for through the wafer via	United States of America	14 Sep 2007	12/442351		
81382857	006822JP1	Network of vias for through the wafer via	Japan	14 Sep 2007			
81142797	006822EP1	Network of vias for through the wafer via	European Patent	22 Sep 2008	08300978.5		
81382854	006822EP2	Network of vias for through the wafer via	European Patent	14 Sep 2007	07828387.8		
81382851	006822CN1	Network of vias for through the wafer via	China	14 Sep 2007			
81359887	81049881EP01	Method of fabrication of low value resistors in a semiconductor material	European Patent	13 May 2008	08290443.4		
81141947	004971WO1	Mask-Free method for inductor performance improvement	Patent				
			Cooperation	15 May 2007	IB2007/061835		
			Treaty				
81376668	004971US1	Mask-Free method for inductor performance improvement	United States of America	15 May 2007	12/301406		
81141948	004971TW1	Mask-Free method for inductor performance	Taiwan				

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Record ID	Patent Family	App Title	Country	Filed Date	App #	Grant Date	Patent #
		improvement					
81376893	004971JP1	Mask-Free method for inductor performance improvement	Japan	15 May 2007	2009-510801		
81376890	004971EP2	Mask-Free method for inductor performance improvement	European Patent	15 May 2007	07735905.7		
81140422	004971EP1	Mask-Free method for inductor performance improvement	European Patent	18 May 2006	06300487.3		
81376887	004971CN1	Mask-Free method for inductor performance improvement	China	15 May 2007	200780017910.9		
81383223	81057108EP01	3D MOS complementary applications informations to ID388894	European Patent	24 Sep 2008	08290888.9		
81371887	81383082EP01	A new method to fabricate through silicon vias in an interposer and to connect integrated circuits on either side of it	European Patent	15 Oct 2008	08290972.2		
81375158	81383559EP01	Electroless metal selective growth on epoxy resin material in sawn cavities	European Patent	24 Dec 2008	08291239.5		
81387874	81387874	Extremely dense architecture for 3D-via and 3D-capacitor integration	ID Awaiting Evaluation				
81385504	81381828EP01	Embedded structure for barrier layer integrity testing in 3D vias	European Patent	29 Sep 2008	08290913.6		
81372284	81382159EP01	Method to make a wavelength detector in silicon	European Patent	01 Oct 2008	08290924.3		
81131538	005852EP1	TRIPOD PILLAR	European Patent	02 May 2008	08300422.0		
81141883	005852WO1	TRIPOD PILLAR	Cooperation Treaty	30 Apr 2007	IB2007/051598		
81141884	005852TW1	TRIPOD PILLAR	Taiwan	30 Apr 2007	96115329		
81376270	005852CN	TRIPOD PILLAR	China	30 Apr 2007	200780025085.X		
81376274	005852EP2	TRIPOD PILLAR	European Patent	30 Apr 2007	07735708.6		
81376278	005852JP	TRIPOD PILLAR	Japan	30 Apr 2007	2008-508959		
81376282	005852US	TRIPOD PILLAR	United States of America	30 Apr 2007	12/299325		
81342010	81050008EP01	Robust and low-ohmic high-density 3D capacitor	European Patent	02 Nov 2007	07119859.2		
81376250	81050008WO02	Robust and low-ohmic high-density 3D capacitor	Patent Cooperation Treaty	20 Oct 2008	IB2008/054302		
81138085	001923EP1	Ultrahigh-Value and Floating Capacitors in Silicon for Decoupling and Charge Pump Applications	European Patent	08 Nov 2005	05110488.3		
81140442	001923WO1	Ultrahigh-Value and Floating Capacitors in Silicon for Decoupling and Charge Pump Applications	Patent Cooperation Treaty	02 Nov 2008	IB2008/054063		

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Record ID	Patent Family	App Title	Country	Filed Date	App #	Grant Date	Patent #
81140443	001923TW1	Ultrahigh-Value and Floating Capacitors in Silicon for Decoupling and Charge Pump Applications	Taiwan	03 Nov 2006	095140846		
81362811	001923CN1	Ultrahigh-Value and Floating Capacitors in Silicon for Decoupling and Charge Pump Applications	China	02 Nov 2006	200680041421.2		
81362816	001923EP2	Ultrahigh-Value and Floating Capacitors in Silicon for Decoupling and Charge Pump Applications	European Patent	02 Nov 2006	06821292.7		
81362821	001923JP1	Ultrahigh-Value and Floating Capacitors in Silicon for Decoupling and Charge Pump Applications	Japan	02 Nov 2006	2008-539554		
81362826	001923US1	Ultrahigh-Value and Floating Capacitors in Silicon for Decoupling and Charge Pump Applications	United States of America	02 Nov 2006	12/092608		
81138087	001925EP1	High frequency trench capacitor	European Patent	08 Nov 2006	06110471.9		
81140378	001925WO1	High frequency trench capacitor	Cooperation Treaty	03 Nov 2006	IB2006/054102		
81140379	001925TW1	High frequency trench capacitor	Taiwan	08 Nov 2006	095141068		
81362479	001925CN1	High frequency trench capacitor	China	03 Nov 2006	200680041428.4		
81362483	001925EP2	High frequency trench capacitor	European Patent	03 Nov 2006	06821322.2		
81362487	001925JP	High frequency trench capacitor	Japan	03 Nov 2006	2008-539563		
81362491	001925US1	High frequency trench capacitor	United States of America	03 Nov 2006	12/092607		
81143954	007319EP1	High Five: Ultra-High Density Capacitors.	European Patent	10 May 2007	07107974.3		
81364931	007319WO1	High Five: Ultra-High Density Capacitors.	Cooperation Treaty	08 May 2008	IB2008/051624		

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